

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claim 1 (Canceled)

Claim 2 (Withdrawn-Currently Amended): The semiconductor device according to claim [[1]] 6, wherein the ring regions are plural and formed in parallel, each of the plural ring regions being connected to the second base region and the stopper region.

Claim 3 (Withdrawn-Currently Amended): The semiconductor device according to claim [[1]] 6, wherein a resistance of the ring region becomes lower from a side of the second base region toward a side of the stopper region.

Claim 4 (Withdrawn-Currently Amended): The semiconductor device according to claim [[1]] 6, further comprising a sense electrode electrically connected to a part of the ring region, the sense electrode being used for detecting a divided voltage applied to the stopper region.

Claim 5 (Withdrawn-Currently Amended): The semiconductor device according to claim [[1]] 6, wherein a circular ring portion, which is surrounding the second base region in a circular ring shape and connected to the second base region, is formed in an inner most circumferential portion of the ring region on the major surface of the first base region, and the ring region is connected to the second base region via the circular ring portion.

Claim 6 (Currently Amended): A The semiconductor device according to claim 1,  
comprising:

a first base region which is of a first conductivity type;

a second base region which is of a second conductivity type and which is selectively  
formed on a major surface of the first base region;

a stopper region which is of a first conductivity type and which is formed on the  
major surface of the first base region, the stopper region being a predetermined distance away  
from the second base region and surrounding the second base region; and

a ring region which is of a second conductivity type which is formed on the major  
surface of the first base region between the second base region and the stopper region, the  
ring region being spirally around the second base region and electrically connected to the  
second base region and the stopper region; wherein corner auxiliary members are formed in  
corner portions of the ring region, the corner auxiliary members being electrically connected  
to the ring region and having a resistance lower than the ring region, ~~and wherein~~ lengths of  
straight portions which are portions of the ring region excluding the corner portions are equal  
irrespective of whether the straight portions are on an inner circumferential side or on an  
outer circumferential side.

Claim 7-17 (Canceled).

Claim 18 (Withdrawn-Currently Amended): The semiconductor device according to  
claim [[7]] 22, wherein the ring regions are plural and formed in parallel, each of the plural  
ring regions being connected to the second base region and the stopper region.

Claim 19 (Withdrawn-Currently Amended): The semiconductor device according to claim [[7]] 22, wherein a resistance of the ring region becomes lower from a side of the second base region toward a side of the stopper region.

Claim 20 (Withdrawn-Currently Amended): The semiconductor device according to claim [[7]] 22, further comprising a sense electrode electrically connected to a part of the ring region, the sense electrode being used for detecting a divided voltage applied to the stopper region.

Claim 21 (Withdrawn-Currently Amended): The semiconductor device according to claim [[7]] 22, wherein a circular ring portion, which is surrounding the second base region in a circular ring shape and connected to the second base region, is formed in an inner most circumferential portion of the ring region on the major surface of the first base region, and the ring region is connected to the second base region via the circular ring portion.

Claim 22 (Currently Amended): A The semiconductor device according to claim 7, comprising:

a first base region which is of a first conductivity type;

a second base region which is of a second conductivity type and which is selectively formed on a major surface of the first base region;

a stopper region which is of a first conductivity type and which is formed on the major surface of the first base region, the stopper region being a predetermined distance away from the second base region and surrounding the second base region;

a ring region which is of a second conductivity type which is formed on the major surface of the first base region between the second base region and the stopper region, the

ring region being spirally around the second base region and electrically connected to the second base region and the stopper region; wherein corner auxiliary members are formed in corner portions of the ring region, the corner auxiliary members being electrically connected to the ring region and having a resistance lower than the ring region, lengths of straight portions which are portions of the ring region excluding the corner portions are equal irrespective of whether the straight portions are on an inner circumferential side or on an outer circumferential side, and

wherein  $V_{BD}/R_{ring}$  which is a leak current  $I_{leak}$  is designed to be equal to  $1 \text{ mA/cm}^2$  or less, where  $V_{BD}$  is a withstand voltage of the semiconductor device and  $R_{ring}$  is a resistance of the entire ring region.

Claim 23 (New): A semiconductor device comprising:

a first base region which is of a first conductivity type;

a second base region which is of a second conductivity type and which is selectively formed on a major surface of the first base region;

a stopper region which is of a first conductivity type and which is formed on the major surface of the first base region, the stopper region being a predetermined distance away from the second base region and surrounding the second base region; and

a ring region which is formed of a diffused region of a second conductivity type and which is formed within the major surface of the first base region between the second base region and the stopper region, the ring region being spirally around the second base region and electrically connected to the second base region and the stopper region.

Claim 24 (New): The semiconductor device according to claim 23,

wherein corner auxiliary members are formed in corner portions of the ring region, the corner auxiliary members being electrically connected to the ring region and having a resistance lower than the ring region, and

wherein lengths of straight portions which are portions of the ring region excluding the corner portions are equal irrespective of whether the straight portions are on an inner circumferential side or on an outer circumferential side.

Claim 25 (New): The semiconductor device according to claim 23, wherein  $V_{BD}/R_{ring}$  which is a leak current  $I_{leak}$  is designed to be equal to 1 mA/cm<sup>2</sup> or less, where  $V_{BD}$  is a withstand voltage of the semiconductor device and  $R_{ring}$  is a resistance of the entire ring region.

Claim 26 (New): The semiconductor device according to claim 25, wherein corner auxiliary members are formed in corner portions of the ring region, the corner auxiliary members being electrically connected to the ring region and having a resistance lower than the ring region, and

wherein lengths of straight portions which are portions of the ring region excluding the corner portions are equal irrespective of whether the straight portions are on an inner circumferential side or on an outer circumferential side.